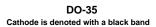


January 2007

1N/FDLL 914/A/B / 916/A/B / 4148 / 4448 **Small Signal Diode**







THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL

LL-34 COLOR BAND MARKING

DEVICE	1ST BAND	2ND BAND
FDLL914	BLACK	BROWN
FDLL914A	BLACK	GRAY
FDLL914B	BROWN	BLACK
FDLL916	BLACK	RED
FDLL916A	BLACK	WHITE
FDLL916B	BROWN	BROWN
FDLL4148	BLACK	BROWN
FDLL4448	BROWN	BLACK

-1st band denotes cathode terminal and has wider width

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{RRM}	Maximum Repetitive Reverse Voltage	100	V
Io	Average Rectified Forward Current	200	mA
I _F	DC Forward Current	300	mA
i _f	Recurrent Peak Forward Current	400	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 4.0	A A
T _{STG}	Storage Temperature Range	-65 to +200	°C
TJ	Operating Junction Temperature	175	°C

^{*} These ratings are limiting values above which the serviceability of the diode may be impaired.

Thermal Characteristics

Symbol	Parameter	Max.	Units	
Symbol	i alametei	1N/FDLL 914/A/B / 4148 / 4448	Omis	
P_{D}	Power Dissipation	500	mW	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W	

These ratings are based on a maximum junction temperature of 200 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

$\textbf{Electrical Characteristics*} \quad \textbf{T}_{A} = 25 \, ^{\circ} \textbf{C unless otherwise noted}$

Symbol	Parameter	Test Conditions	Min.	Max.	Units
V_{R}	Breakdown Voltage	$I_R = 100 \mu A$ $I_R = 5.0 \mu A$	100 75		V V
V _F	1N9 1N914/916/4 1N914A/9 1N9		620 630	720 730 1.0 1.0 1.0	mV mV V V
I _R	Reverse Leakage	$V_R = 20V$ $V_R = 20V$, $T_A = 150$ °C $V_R = 75V$		25 50 5.0	nA μA μA
C _T	Total Capacitance 1N916A/B/4448 1N914A/B/4148	$V_R = 0, f = 1.0MHz$ $V_R = 0, f = 1.0MHz$		2.0 4.0	pF pF
t _{rr}	Reverse Recovery Time	$I_F = 10\text{mA}, V_R = 6.0\text{V } (600\text{mA})$ $I_{rr} = 1.0\text{mA}, R_L = 100\Omega$		4.0	ns

^{*} Non-recurrent square wave PW = 8.3ms

Typical Characteristics

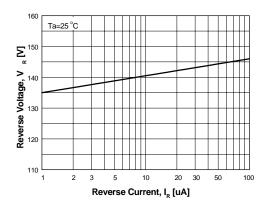


Figure 1. Reverse Voltage vs Reverse Current BV - 1.0 to $100\mu A$

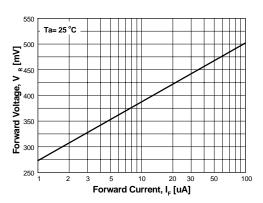
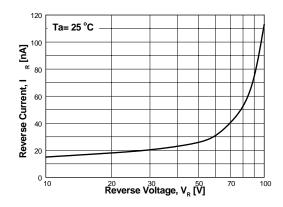


Figure 3. Forward Voltage vs Forward Current VF - 1 to 100 μA



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

Figure 2. Reverse Current vs Reverse Voltage IR - 10 to 100V

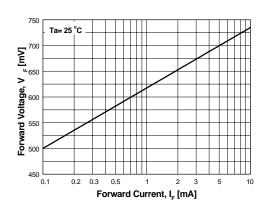


Figure 4. Forward Voltage vs Forward Current VF - 0.1 to 10mA

Typical Characteristics (Continued)

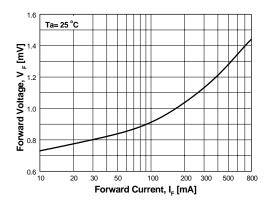
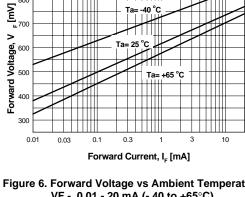


Figure 5. Forward Voltage vs Forward Current VF - 10 to 800mA



900

Typical

Figure 6. Forward Voltage vs Ambient Temperature VF - 0.01 - 20 mA (- 40 to +65°C)

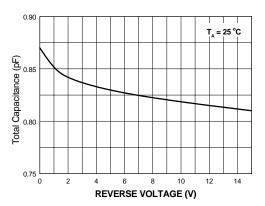
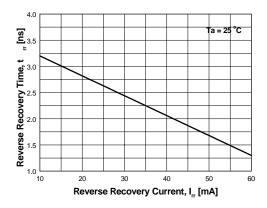


Figure 7. Total Capacitance



 $\label{eq:if_scale} \textbf{IF} = 10 \, \text{mA} \;, \; \; \text{IRR} = 1.0 \; \text{mA} \;, \; \; \text{Rloop} = 100 \; \text{Ohms}$ Figure 8. Reverse Recovery Time vs**Reverse Recovery Current**

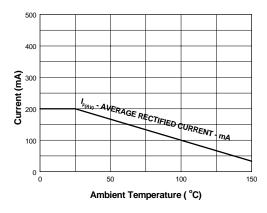


Figure 9. Average Rectified Current (I_{F(AV)}) vs Ambient Temperature (T_A)

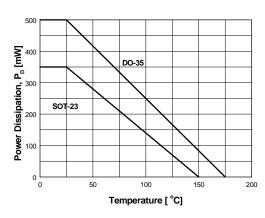


Figure 10. Power Derating Curve

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Rev. I22